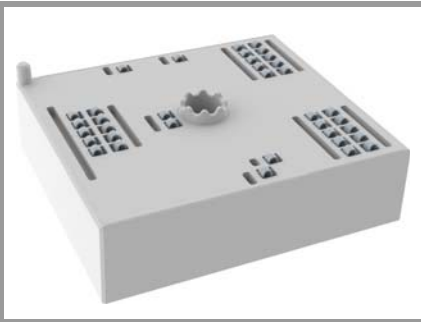


SKiiP 24GB12T4V1



MiniSKiiP® 2 Dual

Half-Bridge

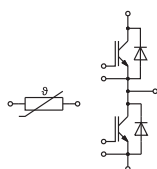
SKiiP 24GB12T4V1

Features*

- Trench 4 IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

Remarks

- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{j,op} = -40 \dots +150^\circ\text{C}$)
- MiniSKiiP "Technical Explanations" and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information

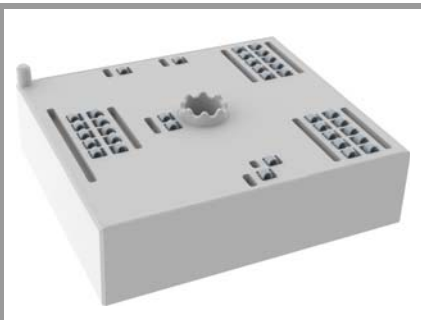


GB

| Absolute Maximum Ratings | | | |
|--------------------------|--------------------------------------------------------------------------------------|---------------------------|------------------|
| Symbol | Conditions | Values | Unit |
| Inverter - IGBT | | | |
| V_{CES} | $T_j = 25^\circ\text{C}$ | 1200 | V |
| I_C | $T_j = 175^\circ\text{C}$ | $T_s = 25^\circ\text{C}$ | 168 |
| | | $T_s = 70^\circ\text{C}$ | 136 |
| I_{Cnom} | | 150 | A |
| I_{CRM} | | 450 | A |
| V_{GES} | | -20 ... 20 | V |
| t_{psc} | $V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$ | $T_j = 150^\circ\text{C}$ | 10 |
| T_j | | -40 ... 175 | $^\circ\text{C}$ |
| Inverse - Diode | | | |
| I_F | $T_j = 175^\circ\text{C}$ | $T_s = 25^\circ\text{C}$ | 157 |
| | | $T_s = 70^\circ\text{C}$ | 125 |
| I_{FRM} | | 300 | A |
| I_{FSM} | 10 ms, sin 180°, $T_j = 150^\circ\text{C}$ | 774 | A |
| T_j | | -40 ... 175 | $^\circ\text{C}$ |
| Module | | | |
| $I_{t(RMS)}$ | $T_{terminal} = 80^\circ\text{C}$, 20 A per spring | 200 | A |
| T_{stg} | module without TIM | -40 ... 125 | $^\circ\text{C}$ |
| V_{isol} | AC sinus 50 Hz, $t = 1\text{ min}$ | 2500 | V |

| Characteristics | | | | | |
|------------------------|-----------------------------------------------------------------|---------------------------|------|------|------------|
| Symbol | Conditions | min. | typ. | max. | Unit |
| Inverter - IGBT | | | | | |
| $V_{CE(sat)}$ | $I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel | $T_j = 25^\circ\text{C}$ | 1.85 | 2.10 | V |
| | | $T_j = 150^\circ\text{C}$ | 2.25 | 2.45 | V |
| V_{CE0} | chipelevel | $T_j = 25^\circ\text{C}$ | 0.80 | 0.90 | V |
| | | $T_j = 150^\circ\text{C}$ | 0.70 | 0.80 | V |
| r_{CE} | $V_{GE} = 15\text{ V}$ chipelevel | $T_j = 25^\circ\text{C}$ | 7.0 | 8.0 | m Ω |
| | | $T_j = 150^\circ\text{C}$ | 10 | 11 | m Ω |
| $V_{GE(th)}$ | $V_{GE} = V_{CE}$, $I_C = 6\text{ mA}$ | 5 | 5.8 | 6.5 | V |
| I_{CES} | $V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$ | $T_j = 25^\circ\text{C}$ | | 1.5 | mA |
| | | | | - | mA |
| C_{ies} | $V_{CE} = 25\text{ V}$ | $f = 1\text{ MHz}$ | 8.80 | | nF |
| C_{oes} | $V_{GE} = 0\text{ V}$ | $f = 1\text{ MHz}$ | 0.58 | | nF |
| C_{res} | | $f = 1\text{ MHz}$ | 0.47 | | nF |
| Q_G | -8 V...+15 V | | 850 | | nC |
| R_{Gint} | $T_j = 25^\circ\text{C}$ | | 5.0 | | Ω |
| $t_{d(on)}$ | $V_{CC} = 600\text{ V}$ $I_C = 150\text{ A}$ | $T_j = 150^\circ\text{C}$ | 136 | | ns |
| t_r | $R_{G on} = 2\ \Omega$ | $T_j = 150^\circ\text{C}$ | 39 | | ns |
| E_{on} | $R_{G off} = 2\ \Omega$ | $T_j = 150^\circ\text{C}$ | 10.8 | | mJ |
| $t_{d(off)}$ | $di/dt_{on} = 4700\text{ A}/\mu\text{s}$ | $T_j = 150^\circ\text{C}$ | 391 | | ns |
| t_f | $di/dt_{off} = 1600\text{ A}/\mu\text{s}$ | $T_j = 150^\circ\text{C}$ | 82 | | ns |
| E_{off} | $V_{GE} = +15/-15\text{ V}$ $L_s = 25\text{ nH}$ | $T_j = 150^\circ\text{C}$ | 15.6 | | mJ |
| $R_{th(j-s)}$ | per IGBT, $\lambda_{paste} = 0.8\text{ W}/(\text{K}^*\text{m})$ | | 0.32 | | K/W |

SKiiP 24GB12T4V1



MiniSKiiP® 2 Dual

Half-Bridge

SKiiP 24GB12T4V1

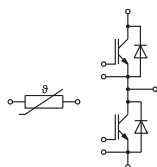
Features*

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| Characteristics | | | | | | |
|---------------------------|----------------------------------------------------------------------------|---------------------------|------|---------------|------|---------------|
| Symbol | Conditions | | min. | typ. | max. | Unit |
| Inverse - Diode | | | | | | |
| $V_F = V_{EC}$ | $I_F = 150\text{ A}$ $V_{GE} = 0\text{ V}$ chipelevel | $T_j = 25^\circ\text{C}$ | | 2.17 | 2.49 | V |
| | | $T_j = 150^\circ\text{C}$ | | 2.11 | 2.42 | V |
| V_{F0} | chipelevel | $T_j = 25^\circ\text{C}$ | | 1.30 | 1.50 | V |
| | | $T_j = 150^\circ\text{C}$ | | 0.90 | 1.10 | V |
| r_F | chipelevel | $T_j = 25^\circ\text{C}$ | | 5.8 | 6.6 | m Ω |
| | | $T_j = 150^\circ\text{C}$ | | 8.1 | 8.8 | m Ω |
| I_{RRM} | $I_F = 150\text{ A}$ | $T_j = 150^\circ\text{C}$ | | 191 | | A |
| Q_{rr} | $di/dt_{off} = 5000\text{ A}/\mu\text{s}$ | $T_j = 150^\circ\text{C}$ | | 25 | | μC |
| E_{rr} | $V_{GE} = -15\text{ V}$ $V_{CC} = 600\text{ V}$ | $T_j = 150^\circ\text{C}$ | | 10.3 | | mJ |
| $R_{th(j-s)}$ | per Diode, $\lambda_{paste}=0.8\text{ W}/(\text{K}\cdot\text{m})$ | | | 0.41 | | K/W |
| Module | | | | | | |
| L_{CE} | | | | 20 | | nH |
| M_s | to heat sink | | 2 | | 2.5 | Nm |
| w | | | | 50 | | g |
| Temperature Sensor | | | | | | |
| R_{100} | $T_c=100^\circ\text{C}$ ($R_{25}=5\text{ k}\Omega$) | | | $493 \pm 5\%$ | | Ω |
| $B_{25/85}$ | $R_{(T)}=R_{25} \cdot \exp[B_{25/85} \cdot (1/T - 1/298)]$, $T[\text{K}]$ | | | 3420 | | K |



GB

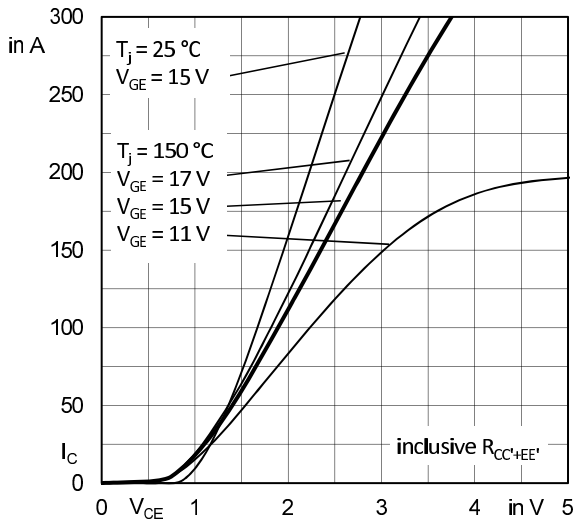


Fig. 1: Typ. output characteristic

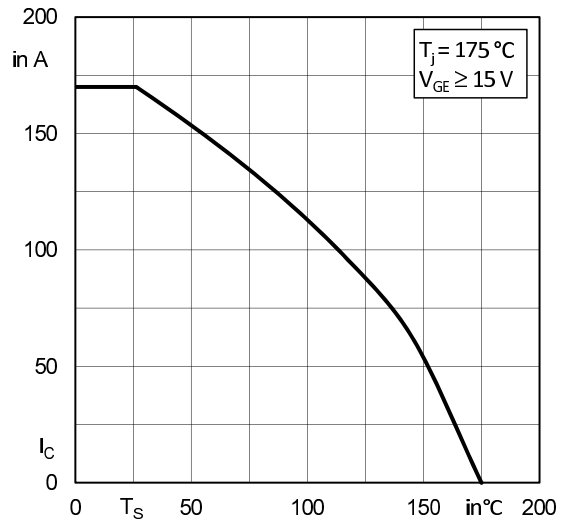


Fig. 2: Rated current vs. temperature $I_C = f(T_S)$

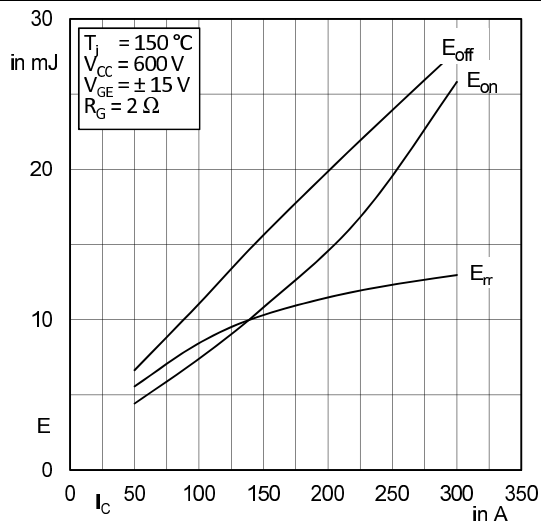


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

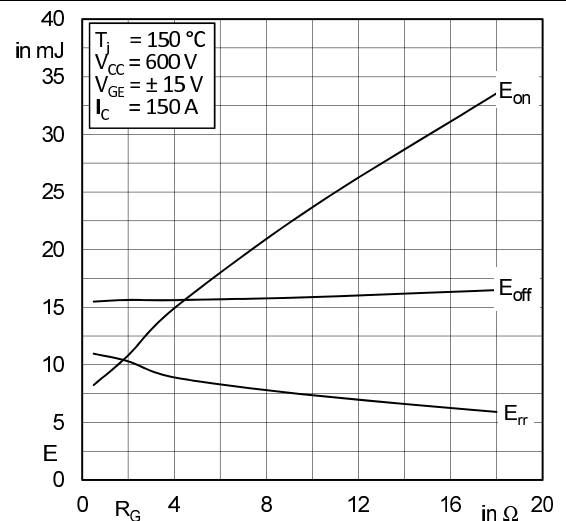


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

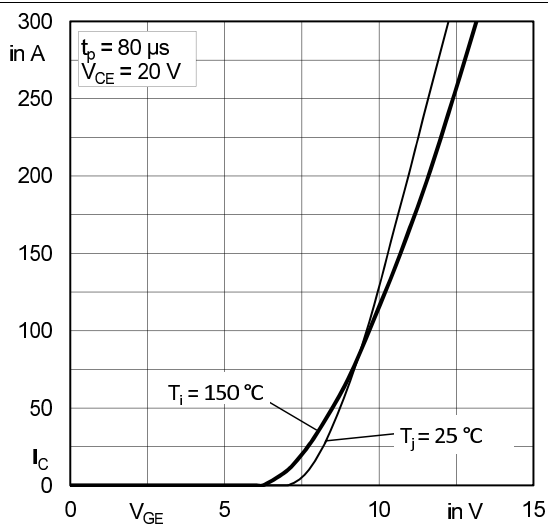


Fig. 5: Typ. transfer characteristic

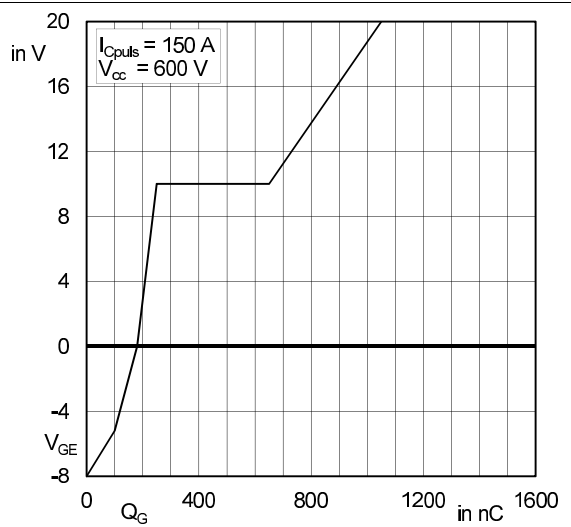


Fig. 6: Typ. gate charge characteristic

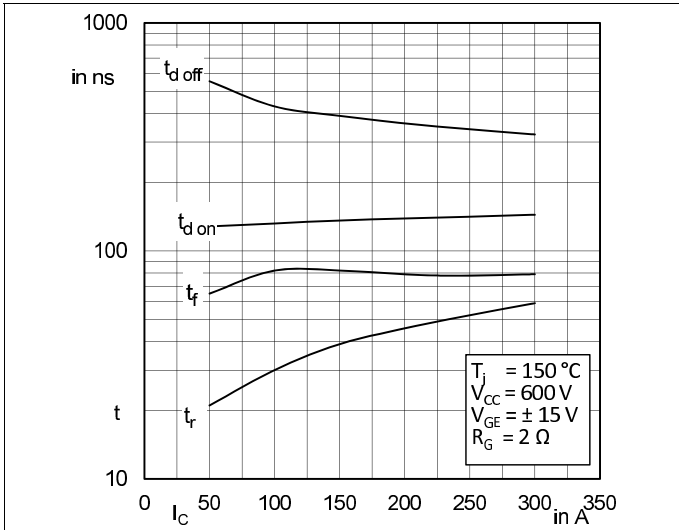


Fig. 7: Typ. switching times vs. I_C

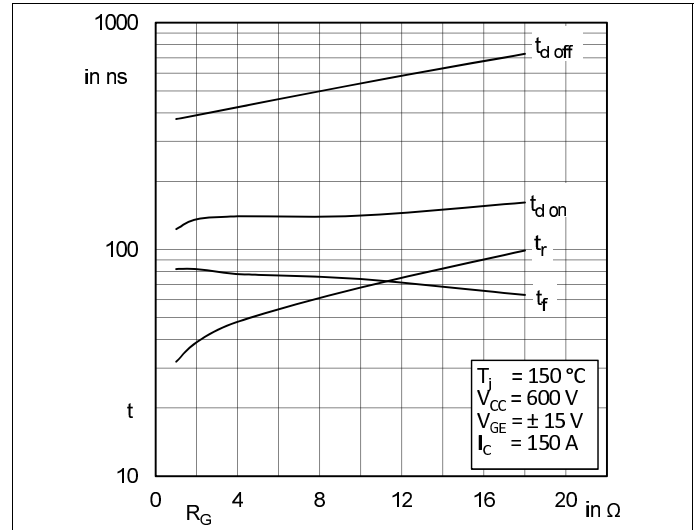


Fig. 8: Typ. switching times vs. gate resistor R_G

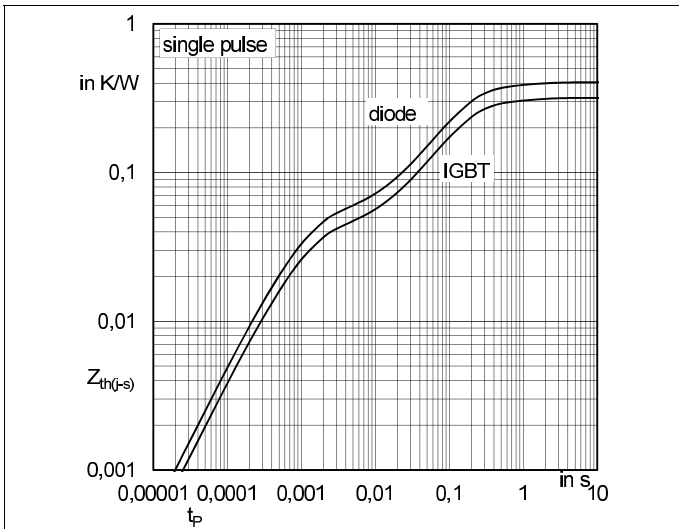


Fig. 9: Typ. transient thermal impedance

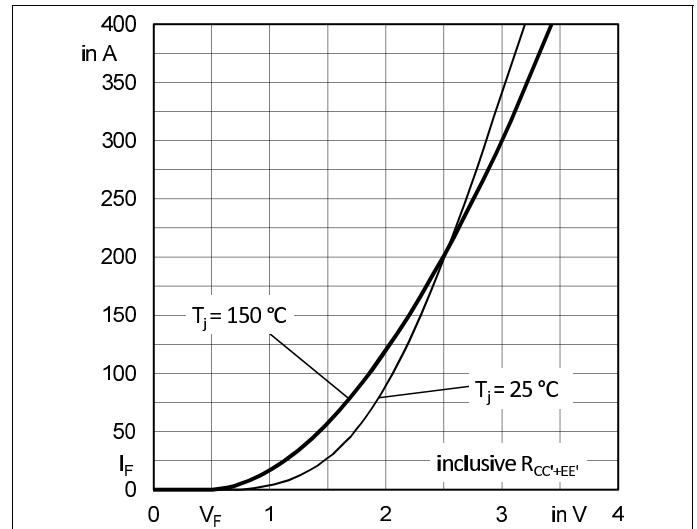


Fig. 10: Typ. CAL diode forward characteristic

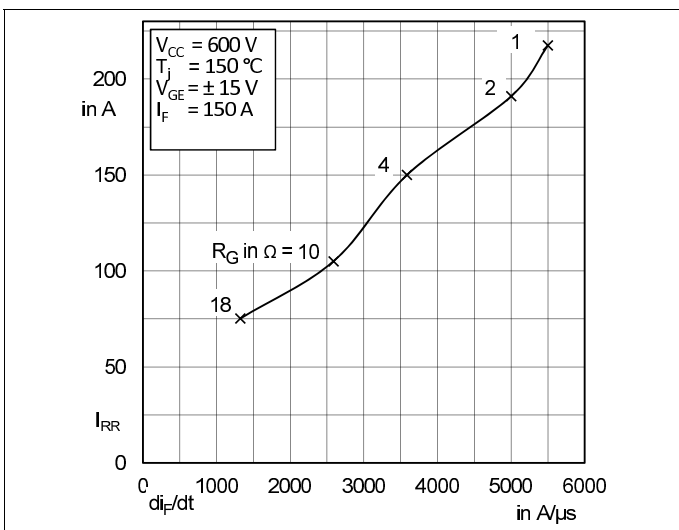


Fig. 11: Typ. CAL diode peak reverse recovery current

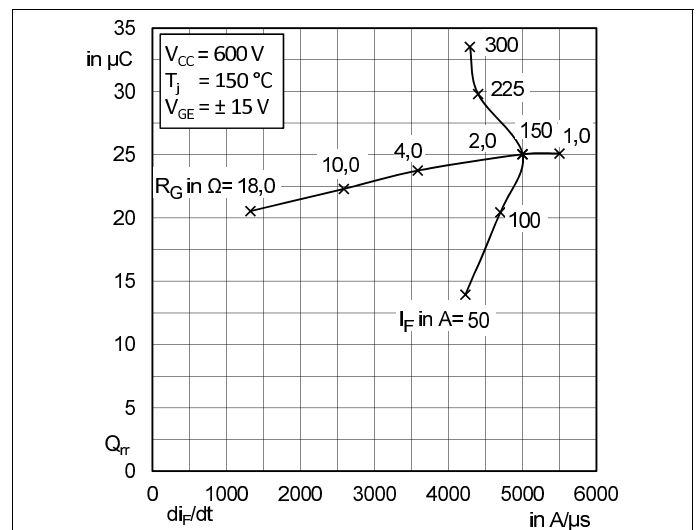
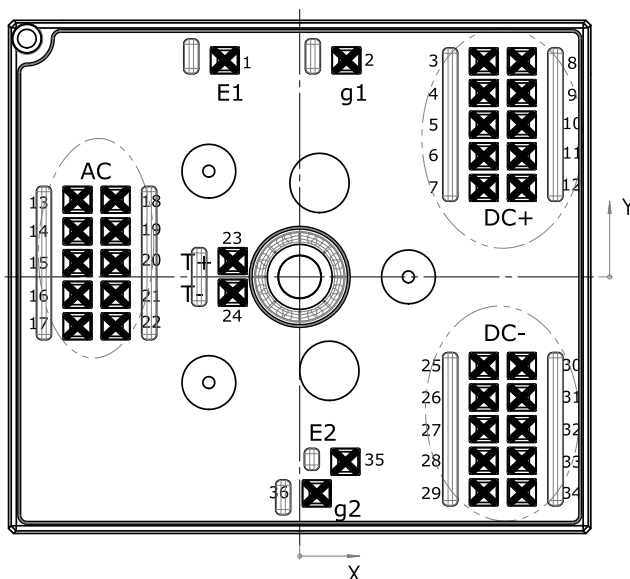


Fig. 12: Typ. CAL diode recovery charge

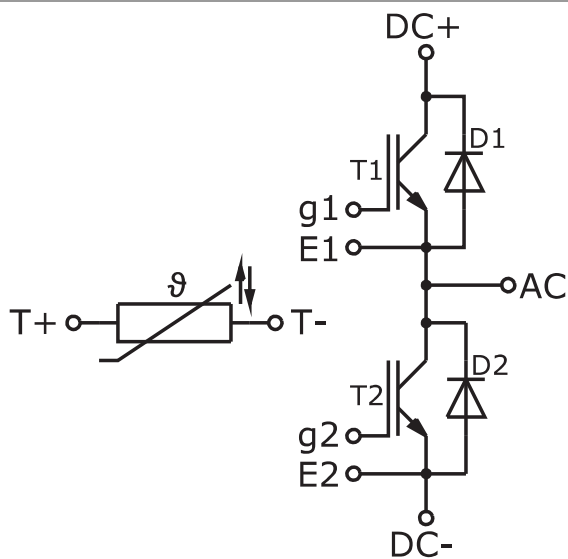
SKiiP 24GB12T4V1

| Pin out | | | | | | | |
|---------|--------|------|----------|-----|--------|-------|----------|
| Pin | X | Y | Function | Pin | X | Y | Function |
| 1 | -7,58 | 21,9 | E1 | 19 | -18,63 | 4,6 | AC |
| 2 | 4,73 | 21,9 | g1 | 20 | -18,63 | 1,4 | AC |
| 3 | 18,63 | 21,8 | DC+ | 21 | -18,63 | -1,8 | AC |
| 4 | 18,63 | 18,6 | DC+ | 22 | -18,63 | -5 | AC |
| 5 | 18,63 | 15,4 | DC+ | 23 | -6,78 | 1,6 | T+ |
| 6 | 18,63 | 12,2 | DC+ | 24 | -6,78 | -1,6 | T- |
| 7 | 18,63 | 9 | DC+ | 25 | 18,63 | -9 | DC- |
| 8 | 22,48 | 21,8 | DC+ | 26 | 18,63 | -12,2 | DC- |
| 9 | 22,48 | 18,6 | DC+ | 27 | 18,63 | -15,4 | DC- |
| 10 | 22,48 | 15,4 | DC+ | 28 | 18,63 | -18,6 | DC- |
| 11 | 22,48 | 12,2 | DC+ | 29 | 18,63 | -21,8 | DC- |
| 12 | 22,48 | 9 | DC+ | 30 | 22,48 | -9 | DC- |
| 13 | -22,48 | 7,8 | AC | 31 | 22,48 | -12,2 | DC- |
| 14 | -22,48 | 4,6 | AC | 32 | 22,48 | -15,4 | DC- |
| 15 | -22,48 | 1,4 | AC | 33 | 22,48 | -18,6 | DC- |
| 16 | -22,48 | -1,8 | AC | 34 | 22,48 | -21,8 | DC- |
| 17 | -22,48 | -5 | AC | 35 | 4,63 | -18,7 | E2 |
| 18 | -18,63 | 7,8 | AC | 36 | 1,73 | -21,9 | g2 |

all values in [mm]



Pinout and Dimensions



Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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